

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

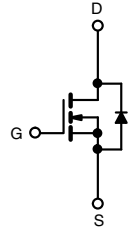
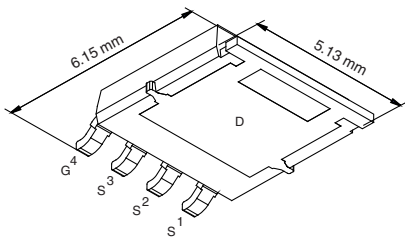


PRODUCT SUMMARY	
V_{DS} (V)	40
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.0063
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.0075
I_D (A)	58
Configuration	Single

FEATURES

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified
- 100 % R_g and UIS Tested
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912

PowerPAK® SO-8L Single



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ858AEP-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	$T_C = 25$ °C	58
		$T_C = 125$ °C	33
Continuous Source Current (Diode Conduction)	I_S	43	A
Pulsed Drain Current ^a	I_{DM}	230	
Single Pulse Avalanche Current	I_{AS}	35	
Single Pulse Avalanche Energy	E_{AS}	61	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25$ °C	48
		$T_C = 125$ °C	16
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	85	°C/W
Junction-to-Case (Drain)			

Notes

- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$		40	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		1.5	2.0	2.5	
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 40\text{ V}$	-	-	1	μA
		$V_{GS} = 0\text{ V}$	$V_{DS} = 40\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 40\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	30	-	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 14\text{ A}$	-	0.0050	0.0063	Ω
		$V_{GS} = 4.5\text{ V}$	$I_D = 10\text{ A}$	-	0.0060	0.0075	
		$V_{GS} = 10\text{ V}$	$I_D = 14\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	-	0.0120	
		$V_{GS} = 10\text{ V}$	$I_D = 14\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	-	0.0150	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 14\text{ V}, I_D = 16\text{ A}$		-	99	-	S
Dynamic^b							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 20\text{ V}, f = 1\text{ MHz}$	-	1951	2450	μF
Output Capacitance	C_{oss}			-	295	370	
Reverse Transfer Capacitance	C_{rss}			-	110	140	
Total Gate Charge ^c	Q_g	$V_{GS} = 10\text{ V}$	$V_{DS} = 20\text{ V}, I_D = 20\text{ A}$	-	36	55	nC
Gate-Source Charge ^c	Q_{gs}			-	8	-	
Gate-Drain Charge ^c	Q_{gd}			-	6	-	
Gate Resistance	R_g	f = 1 MHz		1.5	2.97	4.5	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 2\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		-	10	15	ns
Rise Time ^c	t_r			-	9	14	
Turn-Off Delay Time ^c	$t_{d(off)}$			-	26	40	
Fall Time ^c	t_f			-	8	12	
Source-Drain Diode Ratings and Characteristics^b							
Pulsed Current ^a	I_{SM}			-	-	230	A
Forward Voltage	V_{SD}	$I_F = 15\text{ A}, V_{GS} = 0$		-	0.8	1.1	V

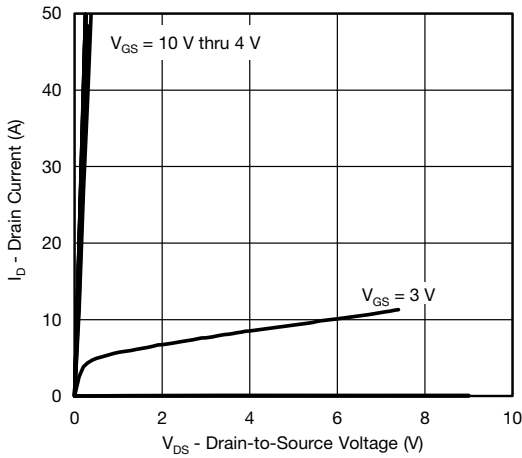
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

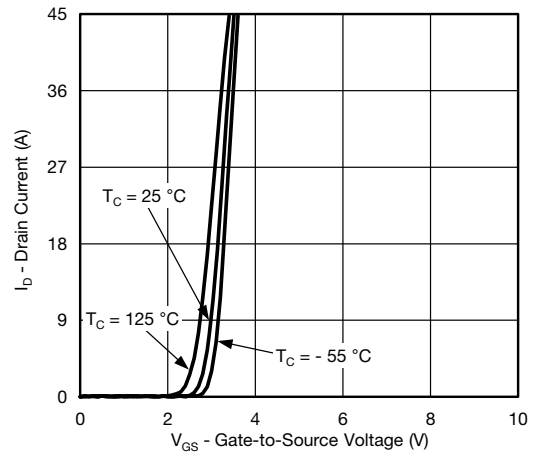
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



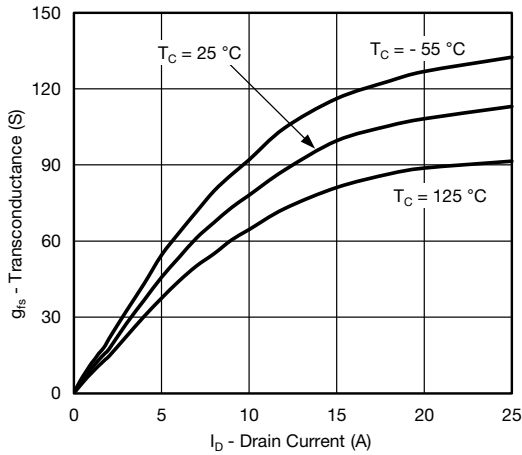
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



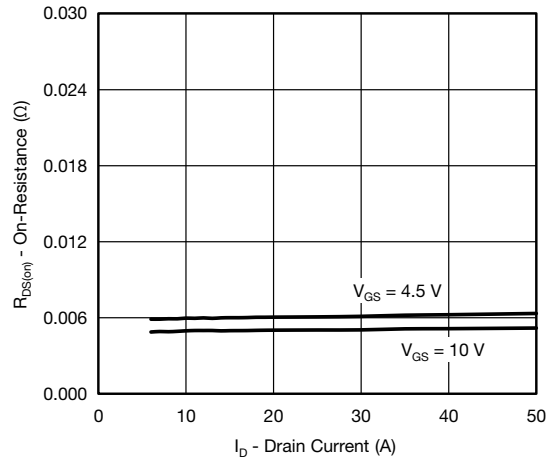
Output Characteristics



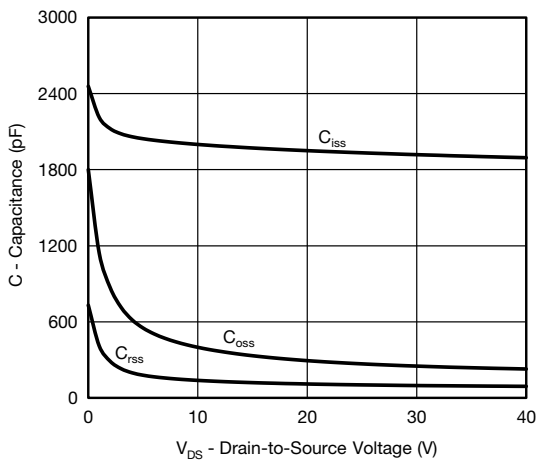
Transfer Characteristics



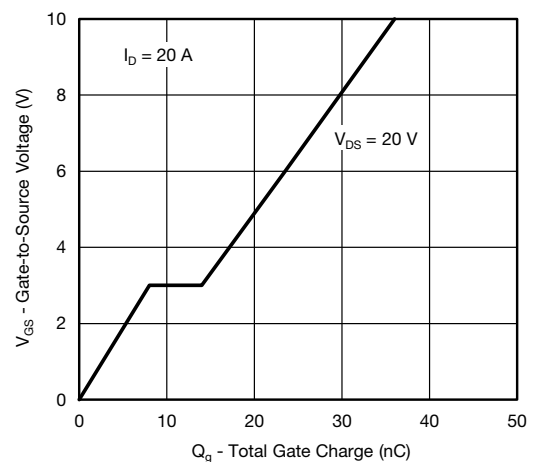
Transconductance



On-Resistance vs. Drain Current



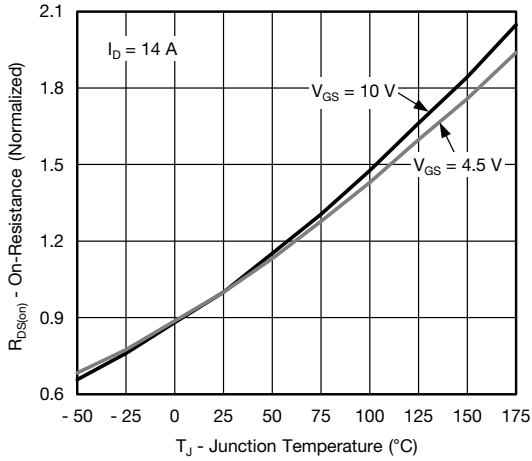
Capacitance



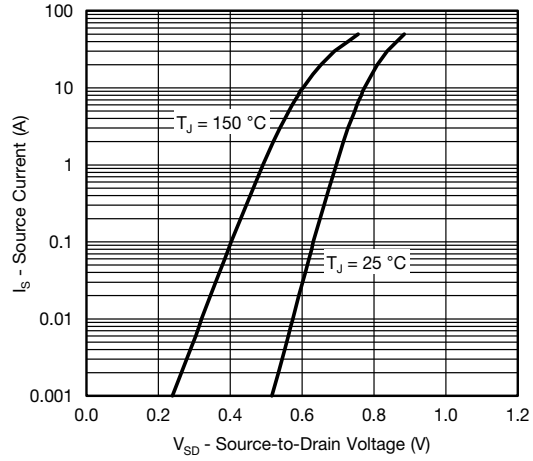
Gate Charge



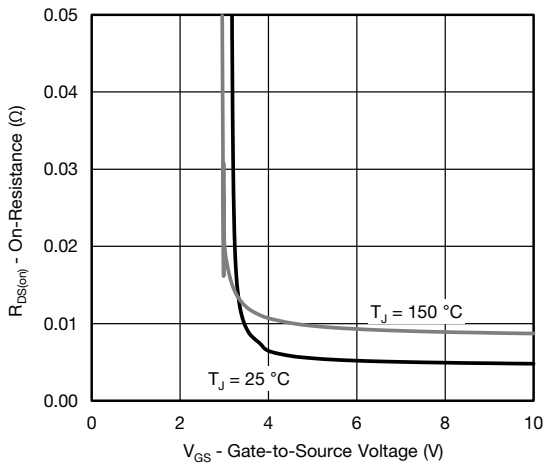
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



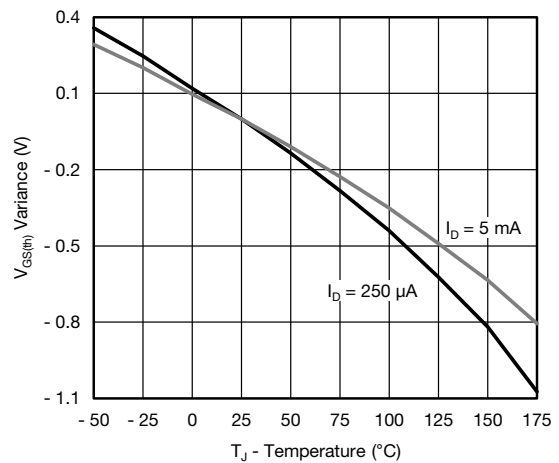
On-Resistance vs. Junction Temperature



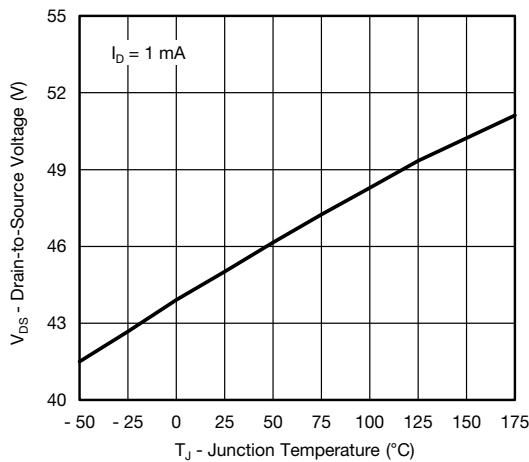
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



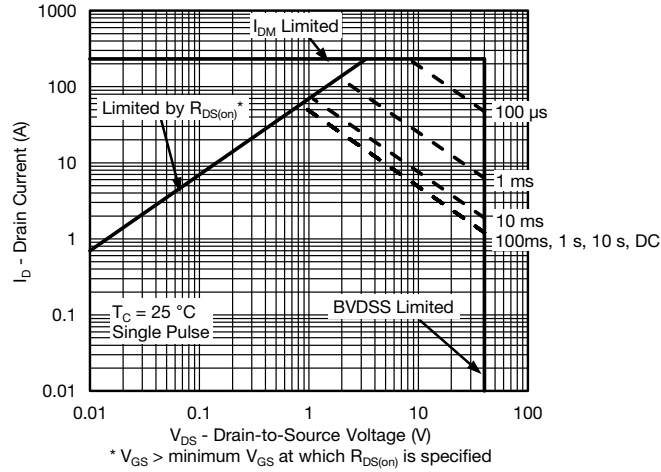
Threshold Voltage



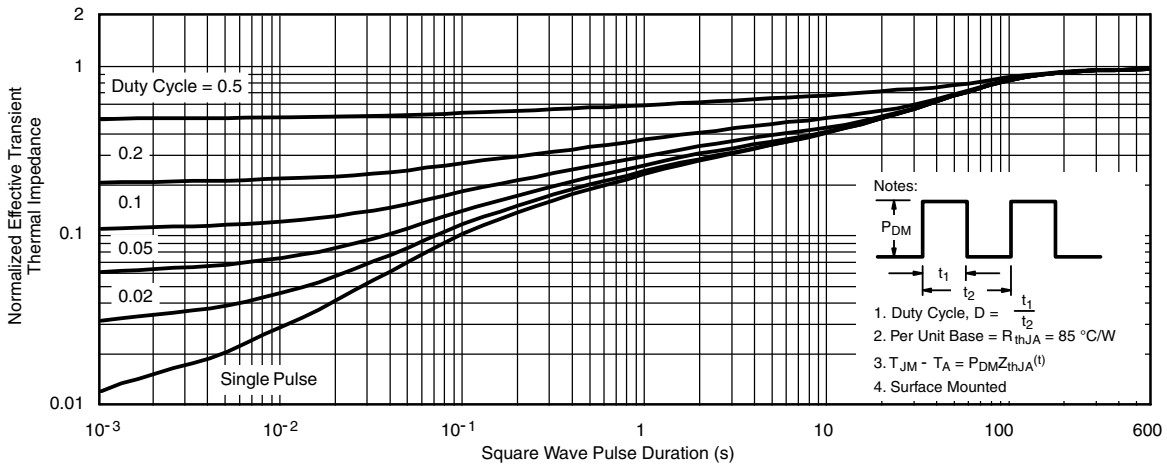
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



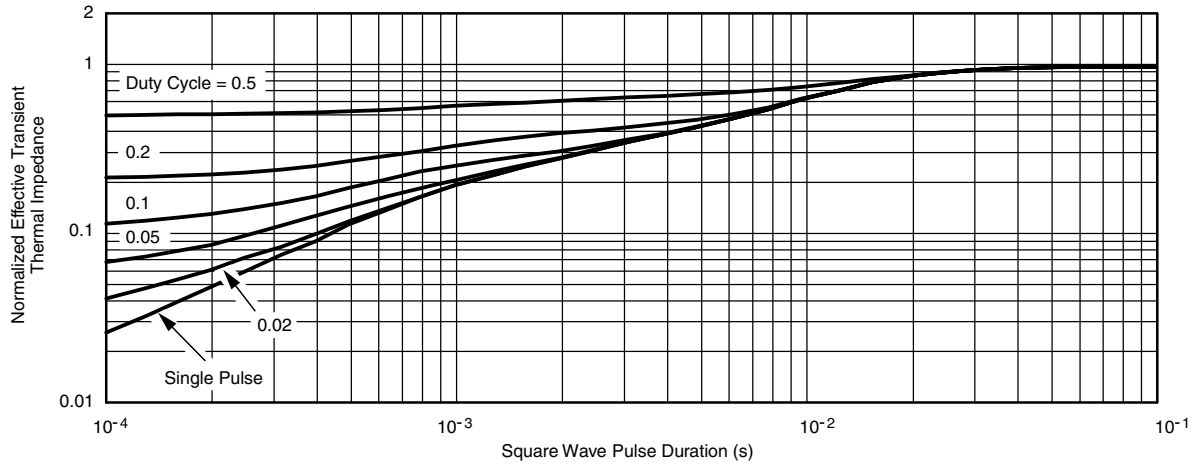
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63470.



PowerPAK® SO-8L

Ordering codes for the SQ rugged series power MOSFETs in the PowerPAK SO-8L package:

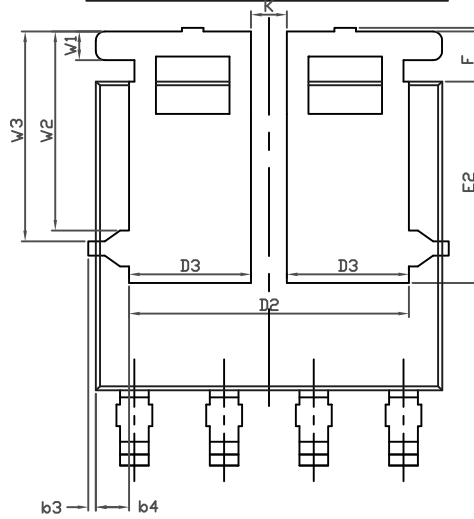
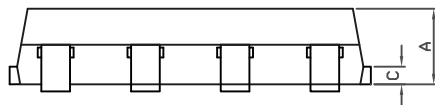
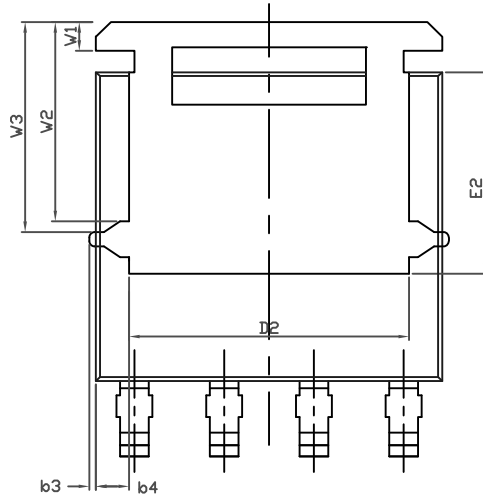
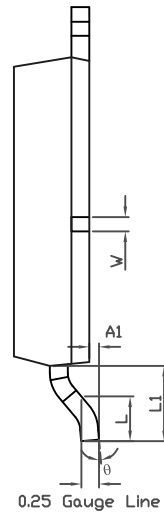
Table with 3 columns: DATASHEET PART NUMBER, OLD ORDERING CODE a, and NEW ORDERING CODE. It lists various MOSFET part numbers and their corresponding new ordering codes.

Note

a. Old ordering code is obsolete and no longer valid for new orders



PowerPAK[®] SO-8L Case Outline for all Parts





DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3	0.094			0.004		
b4	0.47			0.019		
c	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
e	1.27 BSC			0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	2.75	2.85	2.95	0.108	0.112	0.116
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.51			0.020		
W	0.23			0.009		
W1	0.41			0.016		
W2	2.82			0.111		
W3	2.96			0.117		
q	0°	-	10°	0°	-	10°
ECN: C15-1203-Rev. A, 07-Sep-15 DWG: 6044						

Note

- Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads
Dimensions in mm (inches)



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